2N3057A, 2N3700, 2N3700UB

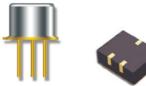


NPN Low Power Silicon Transistor

Rev. V1

Features

- JANS Qualified to MIL-PRF-19500/391
- 2N3700 & 2N3700UB available in JANSR JEDEC registered 2N3700, 2N3057
- Lightweight & Low Power
- Ideal for Space, Military, & other High Reliability **Applications**
- TO-18 (TO-206AA), TO-46 (TO-206AB) Surface Mount UB Package Styles Package







Electrical Characteristics

		Units	Min.	Max.			
Off Characteristics							
Collector - Emitter Breakdown Voltage I _C = 30 mA		V	80	_			
ector - Base Cutoff Current V _{BC} = 140 V		μA	_	10			
V _{EB} = 7 V	I _{EBO1}	μA	_	10			
V _{CE} = 90 V	I _{CES}	nA	_	10			
V _{EB} = 5 Vdc	I _{EBO2}	nA	_	10			
I_{C} = 150 mA, V_{CE} = 10 V I_{C} = 10 mA, V_{CE} = 10 V I_{C} = 500 mA, V_{CE} = 10 V I_{C} = 1 mA, V_{CE} = 10 V		-	100 90 50 15	300 — 300 —			
$I_{\rm C}$ = 150 mA, $I_{\rm B}$ = 15 mA $I_{\rm C}$ = 500 mA, $I_{\rm B}$ = 50 mA		Vdc	_	0.2 0.5			
I _C = 150 mA, I _B = 15 mA		Vdc	_	1.1			
Dynamic Characteristics							
Small-Signal Short-Circuit $I_C = 1 \text{ A}, V_{CE} = 5 \text{ V}, f = 1 \text{ kHz}$ Forward Current Transfer Ratio			80	400			
I _C = 50 mA, V _{CE} = 10 V, f = 20 MHz			5	20			
$V_{CB} = 10 \text{ V}, I_{E} = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$ $V_{CB} = 0.5 \text{ V}, I_{E} = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$		pF	_	12 60			
	$V_{BC} = 140 \text{ V}$ $V_{EB} = 7 \text{ V}$ $V_{CE} = 90 \text{ V}$ $V_{EB} = 5 \text{ Vdc}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 150 \text{ mA}, I_{CE} = 10 \text{ V}, I_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ V}, I_{CE} = 10 \text{ V}, I_{CE} = 10 \text{ V}$	$V_{BC} = 140 \text{ V} \qquad I_{CBO}$ $V_{EB} = 7 \text{ V} \qquad I_{EBO1}$ $V_{CE} = 90 \text{ V} \qquad I_{CES}$ $V_{EB} = 5 \text{ Vdc} \qquad I_{EBO2}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 1 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$ $V_{CE(SAT)}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $V_{BE(SAT)}$ $I_{C} = 10 \text{ MA}, V_{CE} = 10 \text{ V}, f = 20 \text{ MHz}$ $I_{C} = 50 \text{ mA}, V_{CE} = 10 \text{ V}, f = 20 \text{ MHz}$ $I_{C} = 50 \text{ mA}, V_{CE} = 10 \text{ V}, f = 20 \text{ MHz}$ $I_{C} = 10 \text{ V}, I_{E} = 0, 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$ $V_{CB} = 10 \text{ V}, I_{E} = 0, 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$V_{BC} = 140 \text{ V} \qquad \qquad I_{CBO} \qquad \mu A$ $V_{EB} = 7 \text{ V} \qquad \qquad I_{EBO1} \qquad \mu A$ $V_{CE} = 90 \text{ V} \qquad \qquad I_{CES} \qquad nA$ $V_{EB} = 5 \text{ Vdc} \qquad \qquad I_{EBO2} \qquad nA$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA}, I_{B} = 50 \text{ mA}$ $V_{CE(SAT)} \qquad Vdc$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $V_{CE(SAT)} \qquad Vdc$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA}, I_{CE} = 10 \text{ V}, I_{CE} = 10 \text{ V}$ $I_{C} = 100 \text{ V}, I_{CE} = 100 \text{ V}, I_{CE} = 100 \text{ V}$ $I_{CE} = 100 \text{ V}, I_{CE} = 100 \text{ V}$ $I_{CE} = 100 \text{ V}, I_{CE} = 100 \text{ V}$	$V_{BC} = 140 \text{ V} \qquad I_{CBO} \qquad \mu A \qquad -$ $V_{CE} = 90 \text{ V} \qquad I_{CES} \qquad nA \qquad -$ $V_{EB} = 5 \text{ Vdc} \qquad I_{EBO2} \qquad nA \qquad -$ $V_{EB} = 5 \text{ Vdc} \qquad I_{EBO2} \qquad nA \qquad -$ $I_{C} = 150 \text{ mA, } V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA, } V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA, } V_{CE} = 10 \text{ V}$ $I_{C} = 1 \text{ mA, } V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA, } I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA, } I_{B} = 50 \text{ mA}$ $V_{CE(SAT)} \qquad Vdc \qquad -$ $I_{C} = 150 \text{ mA, } I_{B} = 15 \text{ mA}$ $V_{CE(SAT)} \qquad Vdc \qquad -$ $I_{C} = 150 \text{ mA, } I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA, } I_{B} = 15 \text{ mA}$ $I_{C} = 500 \text{ mA, } I_{CE} = 10 \text{ V, } I_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA, } I_{CE} = 10 \text{ V, } I_{CE} = 10 \text{ V}$ $I_{C} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ MHz}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ MHz}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ MHz}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ MHz}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ MHz}$ $I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V, } I_{CE} = 100 \text{ V}$			

Safe Operating Area

DC Tests: T_C = +25 °C, I Cycle, t = 10 ms Test 1: $V_{CE} = 10 \text{ V}, I_{C} = 180 \text{ mA}$ Test 2: V_{CE} = 40 V, I_{C} = 50 mA $V_{CE} = 80 \text{ V}, I_{C} = 15 \text{ mA}$ Test 3:

^{1.} Pulse Test: Pulse Width = 300 µs, Duty Cycle ≤ 2%.

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Absolute Maximum Ratings

Ratings	Symbol	Value
Collector - Emitter Voltage	V _{CEO}	80 V
Collector - Base Voltage	V _{CBO}	140 V
Emitter - Base Voltage	V _{EBO}	7 V
Collector Current	Ic	1 A
Total Power Dissipation @ $T_A = 25^{\circ}C^2$ @ $T_C = 25^{\circ}C^3$	P _T	0.5 W 1.0 W
Operating & Storage Temperature Range	T _{OP} , T _{STG}	-65°C to +200°C

^{2.} Derate linearly @ 2.85 mW / $^{\circ}$ C for T_{A} = 25 $^{\circ}$ C

Thermal Characteristics

Characteristics	Symbol	Max. Value
Thermal Resistance, Junction to Case	$R_{ heta JC}$	150°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	325°C/W

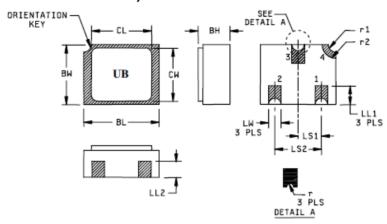
^{3.} Derate linearly @ 10.3 mW / °C for T_C = 25 °C

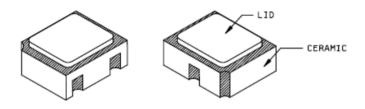


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Outline Drawing (UB Surface Mount)





Symbol	Inc	hes	Millimeters		Note
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	

	Dimensions				
Symbol	Inches Millimeters		neters	Note	
	Min	Max	Min	Max	
LS_1	.036	.040	0.91	1.02	
LS_2	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
\mathbf{r}_1		.012		.305	
r_2		.022		.559	

NOTES:

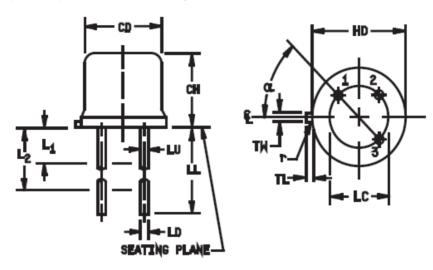
- 1. Dimensions are in inches.
- 2. Millimeters are given for general information only.
- Hatched areas on package denote metalized areas.
- Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
- 5. In accordance with ASME Y14.5M, diameters are equivalent to \$\phi\$x symbology.



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Outline Drawing (TO-46) for 2N3057 only



	Dimensions				
Symbol	Inches		Millimeters		Note
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.065	.085	1.65	2.16	
HD	.209	.230	5.31	5.84	
LC	.10	.100 TP		2.54 TP	
LD	.016	.021	0.41	0.53	7
LL	.500	1.750	12.70	44.45	7
LU	.016	.019	0.41	0.48	7
L1		.050		1.27	7
L2	.250		6.35		7
TL	.028	.048	0.71	1.22	3
TW	.036	.046	0.91	1.17	2
r		.007		0.18	10, 11
α	45° TP		45°	TP	6

NOTES:

- 1. Dimension are in inches.
- 2. Millimeters are given for general information only.
- 3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 4. Dimension TL measured from maximum HD.
- Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
- Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
- 7. All three leads.
- The collector shall be internally connected to the case.
- 9. Dimension r (radius) applies to both inside comers of tab.
- In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
- 11. Lead 1 = emitter, lead 2 = base, lead 3 = collector.

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